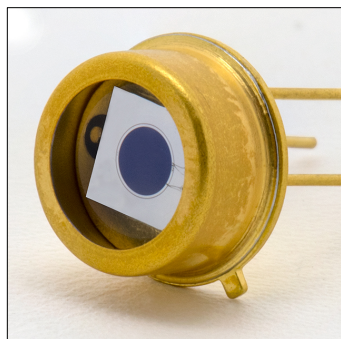


**FEATURES**

- Circular Active Area
- Ideal for 225-400 nm Detection
- 100% Internal QE
- Welded Cap with UV Glass Window

Electro-Optical Characteristics at 25°C

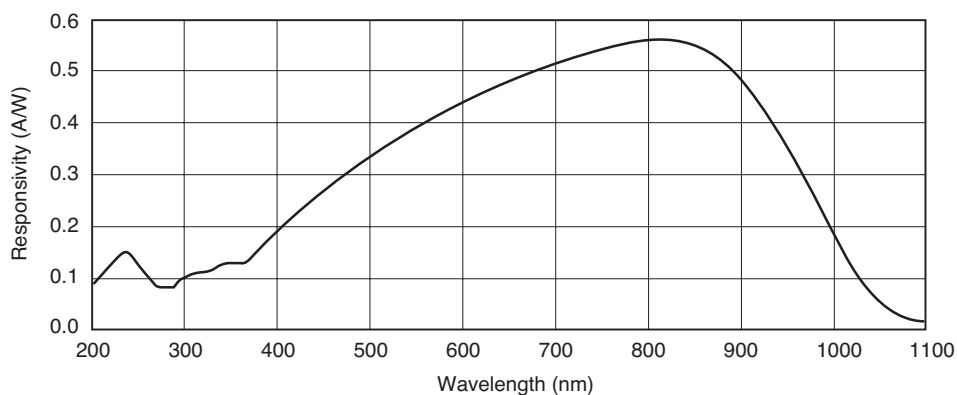
Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	Φ 2.5 mm		5		mm ²
Responsivity	@ 254 nm, $V_R = 0$ V	0.09	0.115		A/W
Dark Current, I_{dr}	$V_R = 6$ V			1	nA
Reverse Breakdown Voltage, V_R	$I_R = 1$ μ A	25	50		Volts
Capacitance, C	$V_R = 0$ V		500	1500	pF
Response Time	$V_R = 0$ V		1	2	μ sec

Thermal Parameters

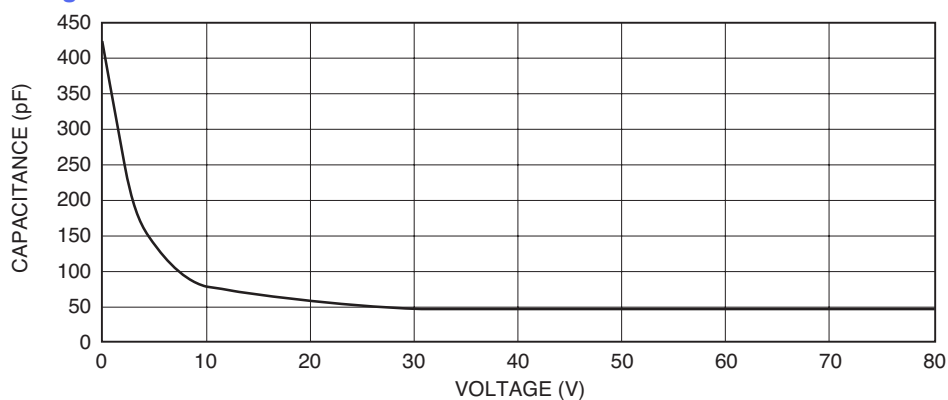
Storage and Operating Temperature Range	Units
Storage Temperature Range	-20°C to 80°C
Lead Soldering Temperature ¹	240°C

¹0.0625" from case for 10 seconds.

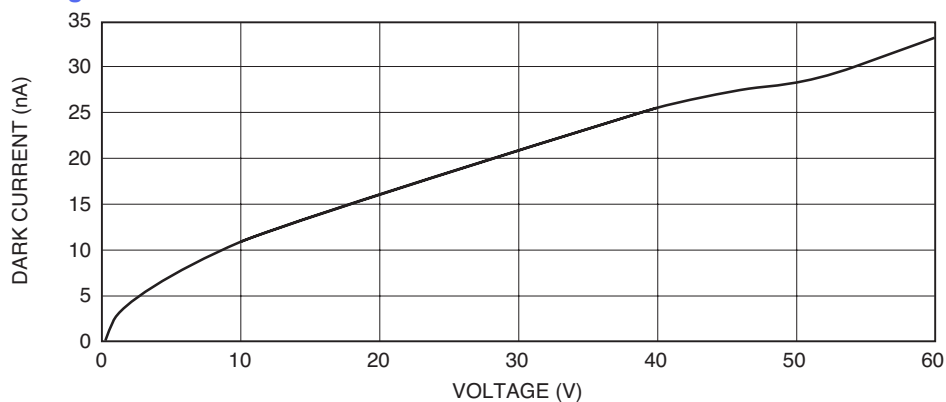
Typical Photon Responsivity



Capacitance vs. Voltage



Dark Current vs. Voltage

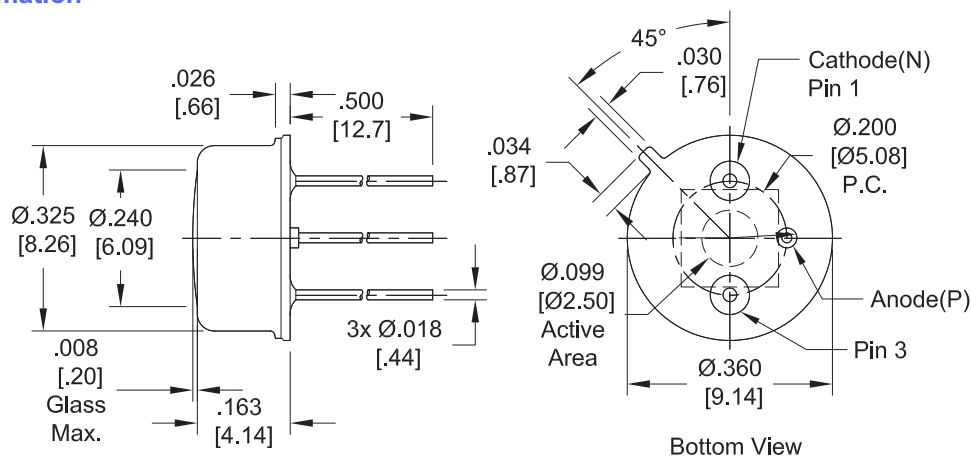


海纳光学

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Package Information

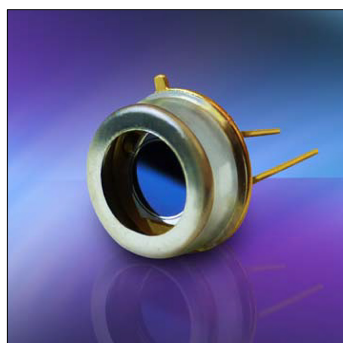


Dimensions are in inch [metric] units.



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FEATURES

- Circular Active Area
- Ideal for 193-400 nm Detection
- 100 % Internal QE
- No Cap for Maximum Responsivity
- Sacrificial Cap Taped on for Shipping Purposes

Electro-Optical Characteristics at 25 °C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	Φ 4.1 mm		13.2		mm ²
Responsivity	(see graph on next page)	0.105	0.115	0.125	A/W
Shunt Resistance	$V_F = \pm 10$ mV	100	1000		Mohms
Reverse Breakdown Voltage, V_R	$I_R = 1$ μ A	10			Volts
Capacitance, C	$V_R = 0$ V		3	7	nF
Response Time	$V_R = 0$ V			4	μ sec

Thermal Parameters

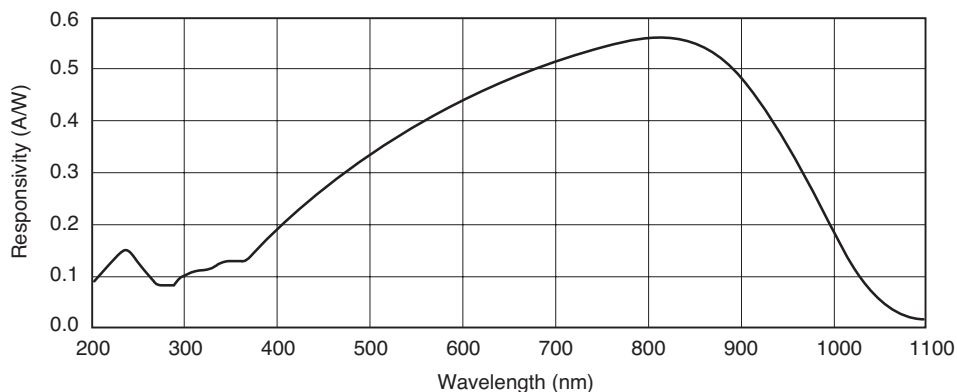
Storage and Operating Temperature Range	Units
Storage Temperature Range	-20°C to 80°C
Operating Temperature Range	80°C
Lead Soldering Temperature ¹	240°C

¹ 0.0625" from case for 10 seconds.

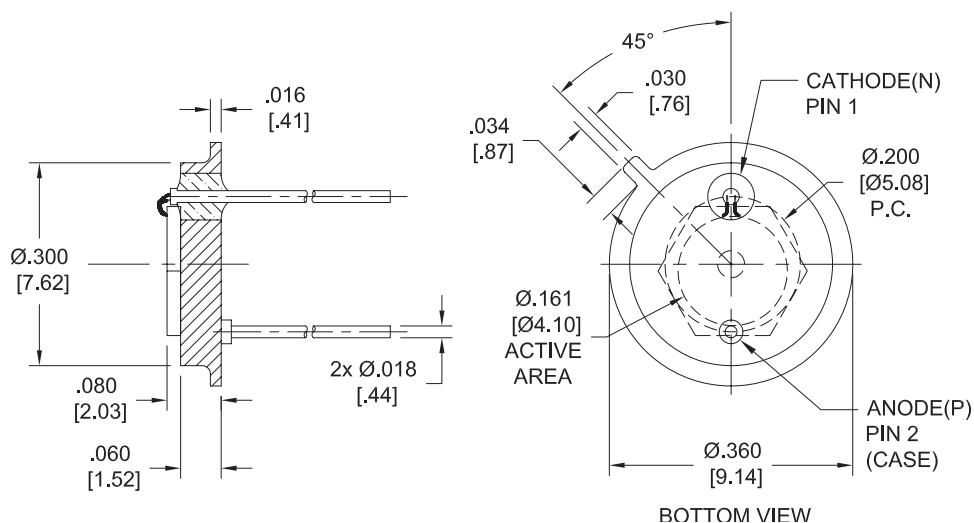
Shipped with temporary cover to protect the photodiode and wire bonds.

Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.

Typical Photon Responsivity



Package Information



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FEATURES

- Circular Active Area
- Ideal for Electron Detection
- 100% Internal QE
- TO-8 Package

Electro-Optical Characteristics at 25°C

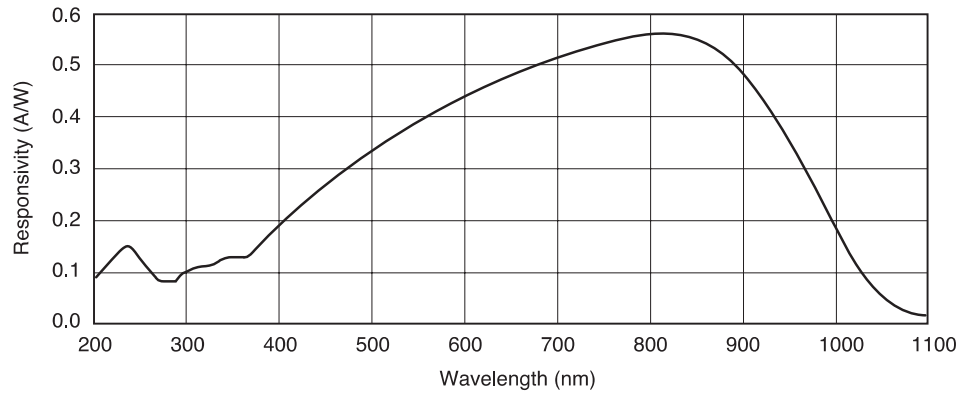
Parameters	Test Conditions	Min	Typ	Max	Units
Active Area ¹	Φ 4.9 mm		19		mm ²
Responsivity	(see graph next page)				A/W
Reverse Breakdown Voltage, V _R	I _R = 1 μA		20		Volts
Capacitance, C	V _R = 0 V		1.2	1.5	nF
Rise Time	RL = 50 Ω, V _R = 0 V			1	us
Shunt Resistance	V _f = ±10 mV	50	100		MOhms
Dark Current	V _R = 13 V			30	nA

¹ Die active area = Φ5.5 mm, aperture size = Φ4.9 mm.

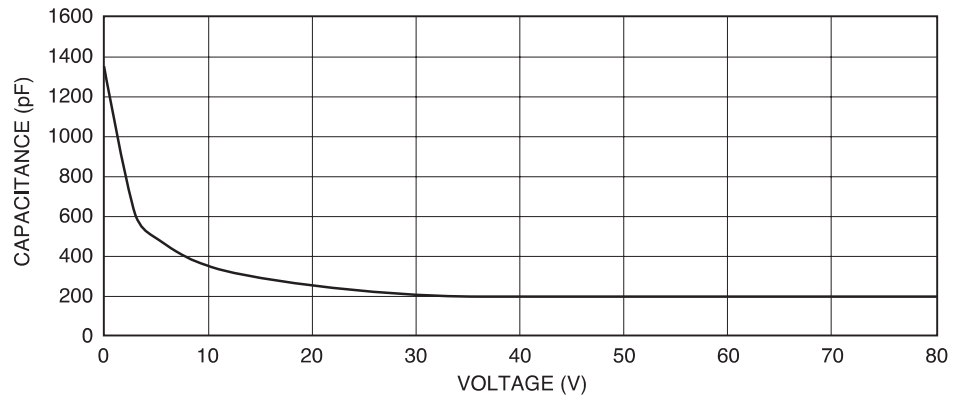
Thermal Parameters

Storage and Operating Temperature Range	Units
Storage Temperature Range	-20°C to 100°C
Operating Temperature Range	20°C to 80°C
Lead Soldering Temperature ¹	240°C

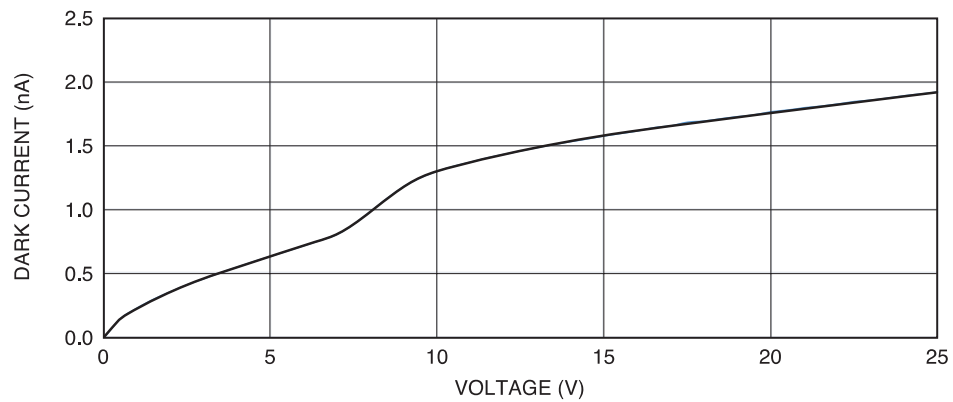
Typical Photon Responsivity



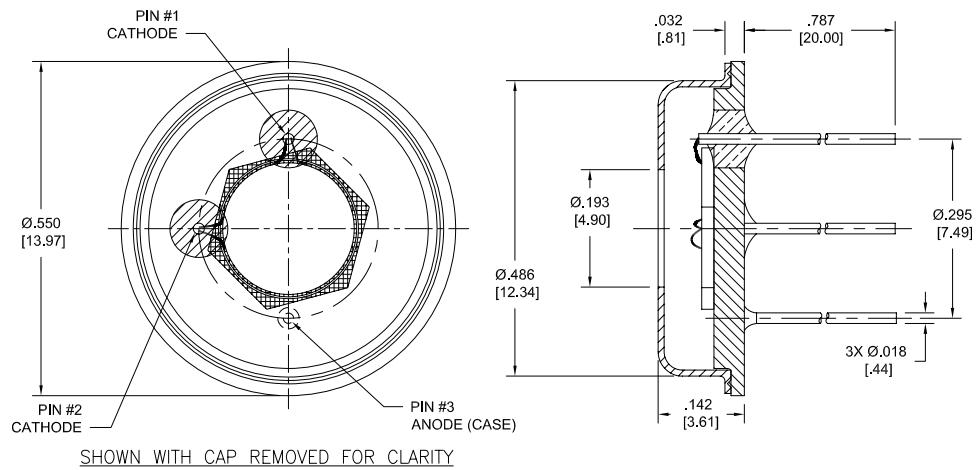
Capacitance vs. Voltage



Dark Current vs. Voltage



Package Information

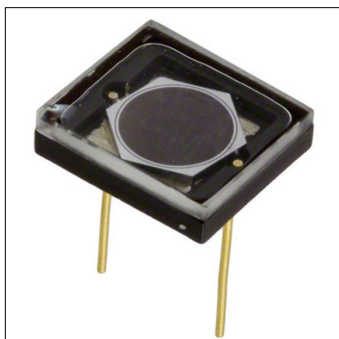


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FEATURES

- Circular Active Area
- Ideal for 190-400 nm Detection
- 100% Internal QE
- UV Quartz Window Epoxy Bonded in Place

Electro-Optical Characteristics at 25 °C

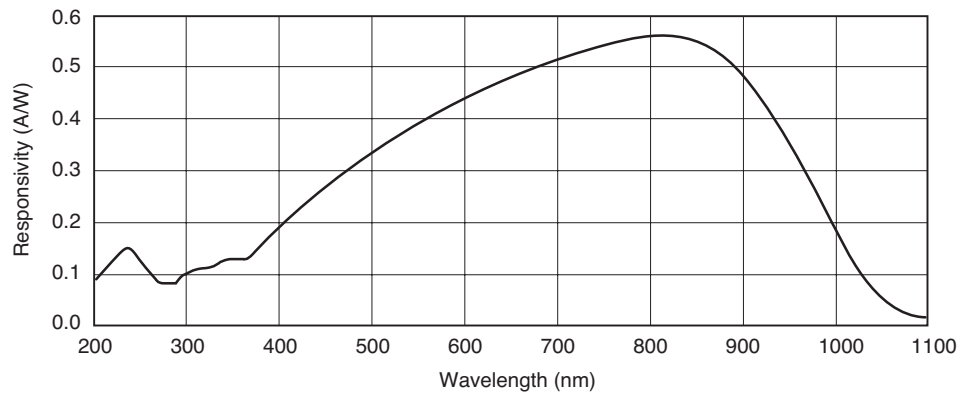
Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	Φ 5.5 mm		24		mm ²
Responsivity	(see graph on next page)	0.105	0.115		A/W
Shunt Resistance	$V_F = \pm 10$ mV	50	100		MOhms
Reverse Breakdown Voltage, V_R	$I_R = 1$ μ A	10	50		Volts
Capacitance, C	$V_R = 0$ V		1.2	1.5	nF
Rise Time	$V_R = 0$ V			1	us

Thermal Parameters

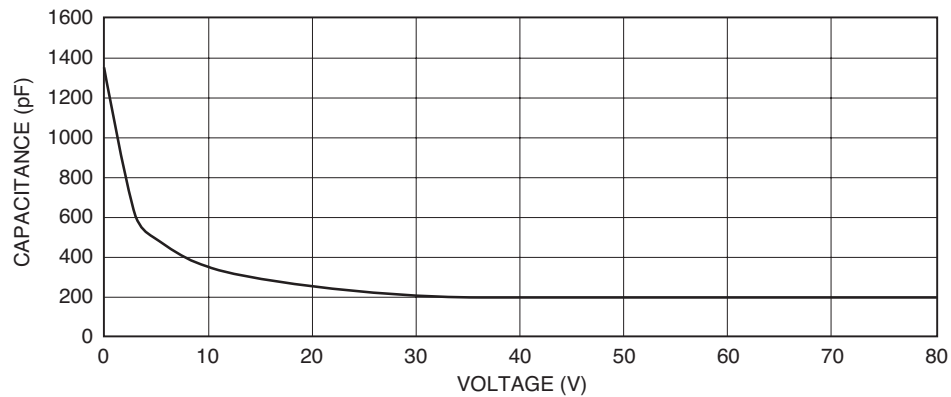
Storage and Operating Temperature Range	Units
Storage Temperature Range	-20° to 80°C
Lead Soldering Temperature ¹	260°C

¹0.0625" from case for 10 seconds.

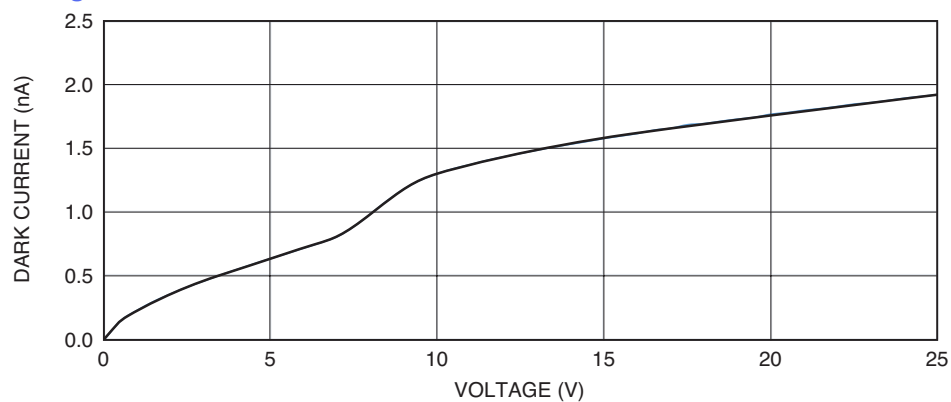
Typical Photon Responsivity



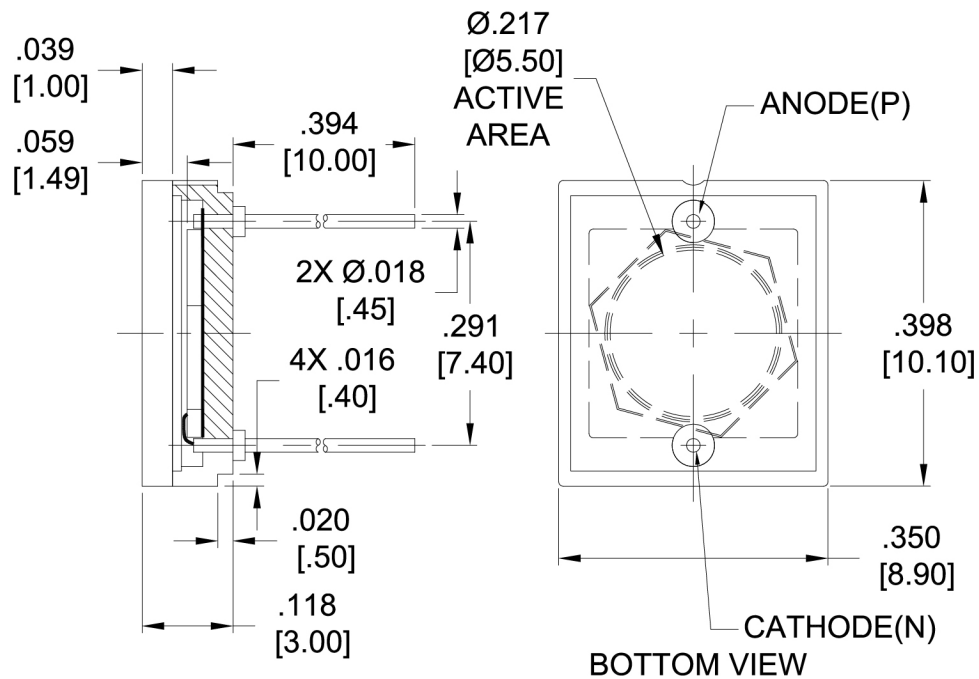
Capacitance vs. Voltage



Dark Current vs. Voltage

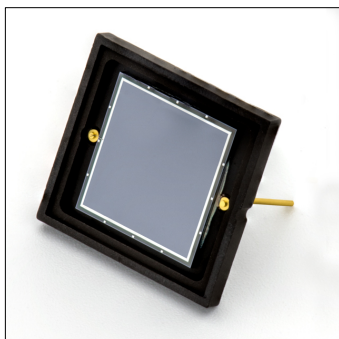


Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.



FEATURES

- Square Active Area
- Ideal for 190-400 nm Detection
- 100% Internal QE
- Excellent UV Response
- Protective Cover Plate²

Electro-Optical Characteristics at 25 °C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	10 mm x 10 mm		100		mm ²
Responsivity	(see graph on next page)	0.08	0.09		A/W
Shunt Resistance	@ ± 10 mV	20			MOhms
Reverse Breakdown Voltage, V _R	I _R = 1 µA	5	10		Volts
Capacitance, C	V _R = 0 V		1	3	nF
Response Time	RL = 50 Ω, V _R = 10 V			10	usec

Thermal Parameters

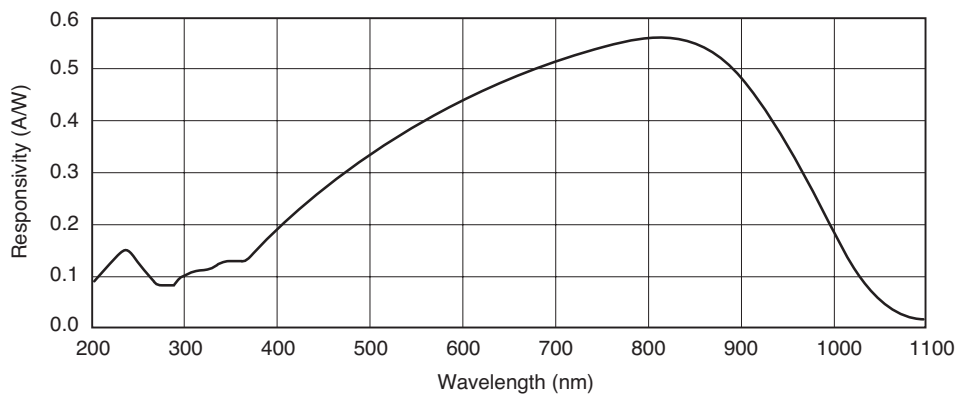
Storage and Operating Temperature Range	Units
Storage Temperature Range	-20° to 100°C
Operating Temperature Range	-20° to 80°C
Lead Soldering Temperature ¹	240°C

¹ 0.08" from case for 10 seconds.

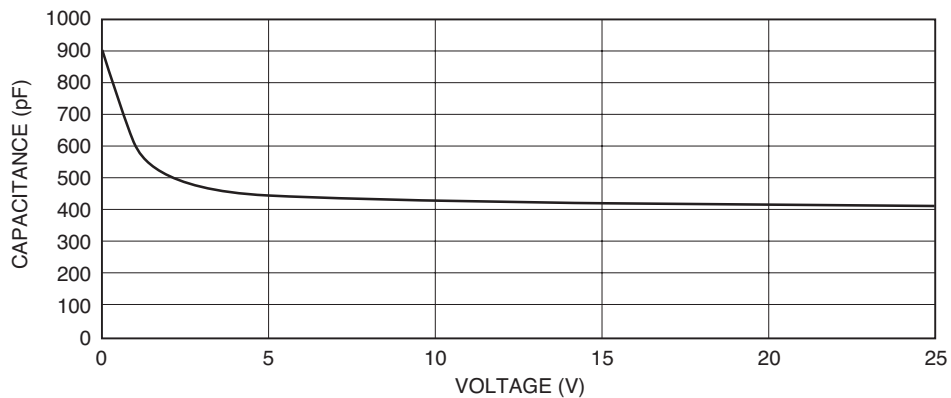
² Shipped with temporary cover to protect the photodiode and wire bonds.

Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.

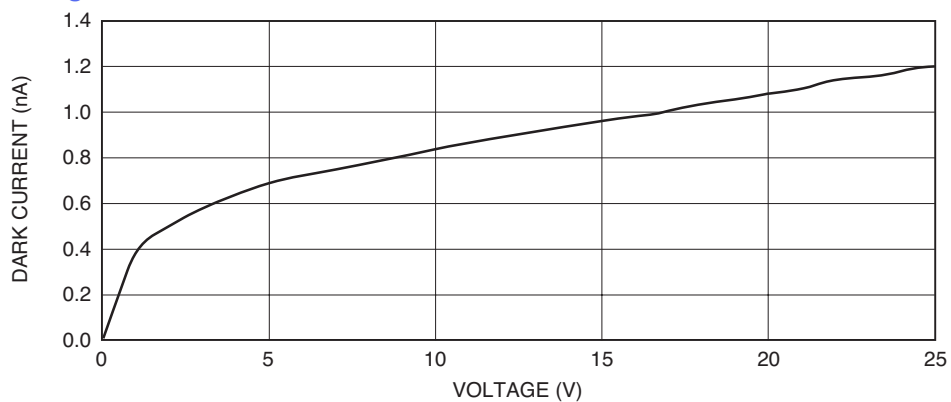
Typical Photon Responsivity



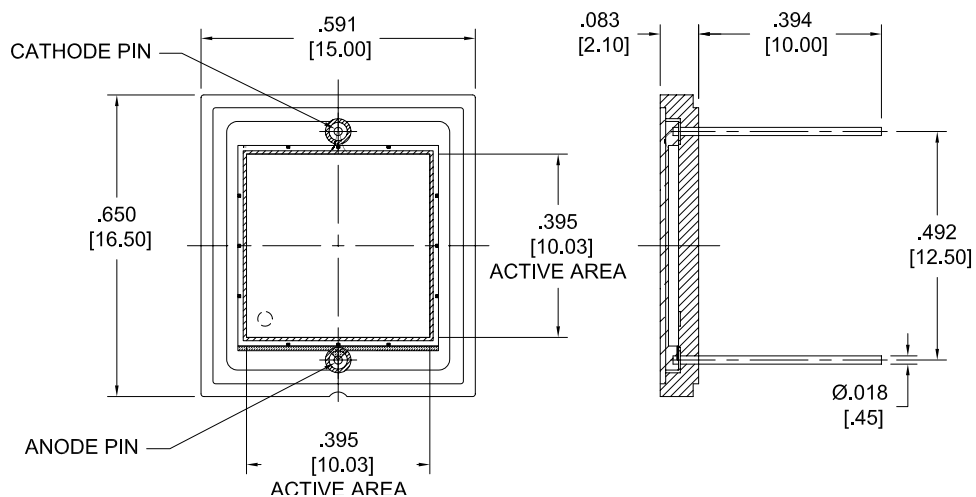
Capacitance vs. Voltage



Dark Current vs. Voltage



Package Information



Dimensions are in inch [metric] units.

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